



Attorney Docket No. 0756-2332

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:	) Group Art Unit: 2825
Takeshi FUKADA et al.	) Examiner: L. Malsawma
Serial No. 09/904,906	) <u>CERTIFICATE OF MAILING</u>
Filed: July 16, 2001	) I hereby certify that this correspondence is
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**INFORMATION DISCLOSURE STATEMENT**

Honorable Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

U.S. Patent Nos. 5,308,998; 5,913,112, and 5,962,870 are in the family of JP 05-114724.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be

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A duplicate copy of this sheet is attached.

Respectfully submitted,



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Eric J. Robinson  
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Robinson Intellectual Property Law Office, P.C.  
PMB 955  
21010 Southbank Street  
Potomac Falls, Virginia 20165  
(571) 434-6789

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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

## **Complete if Known**

Application Number	09/904,906
Filing Date	July 16, 2001
First Named Inventor	Takeshi FUKADA et al.
Group Art Unit	2825
Examiner Name	L. Malsawma
Attorney Docket Number	0756-2332

Sheet 1 of 2

## **U.S. PATENT DOCUMENTS**

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		4,416,952		Nishizawa et al.	11/22/1983	
		4,727,044		Yamazaki	02/23/1988	
		5,147,826		Liu et al.	09/15/1992	
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		6,268,631		Fukada et al.	07/31/2001	

## **FOREIGN PATENT DOCUMENTS**

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		JP	01-144139			06/06/1989		AB
		JP	03-022540			01/30/1991		FULL
		JP	03-024736			02/01/1991		AB

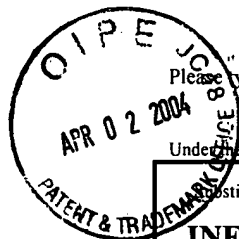
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		JP	03-034434			02/14/1991		AB
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		JP	03-265143			11/26/1991		AB
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		JP	07-131034			05/19/1995		AB
		JP	56-023748			03/06/1981		AB
		JP	04-144139			05/18/1992		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Gang Liu et al., <i>Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing</i> , Appl. Phys. Lett., Vol. 62, No. 20, Pages 2554-2556, May 17, 1993.	
		Gang Liu et al., <i>Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing</i> , Appl. Phys. Lett., Vol. 55, No. 7, Pages 660-662, August 14, 1989.	
		C. Hayzelden et al., <i>In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon</i> , Appl. Phys. Lett., Vol. 60, No. 2, Pages 225-227, January 13, 1992.	
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		R. Kakkad et al., <i>Crystallized Si Films by Low-Temperature Rapid Thermal Annealing of Amorphous Silicon</i> , J. Appl. Phys., Vol. 65, Pages 2069-2072, March 1, 1989.	
		R. Kakkad et al., <i>Low Temperature Selective Crystallization of Amorphous Silicon</i> , Journal of Non-Crystalline Solids, Vol. 115, Pages 66-68, August 1, 1989.	
		A.V. Dvurechenskii et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol., Vol. 95, Pages 635-640, January 1, 1986.	
		T. Hempel et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Vol. 85, No. 11, Pages 921-924, March 1, 1993.	
		E. Korin et al., <i>Crystallization of Amorphous Silicon Films Using a Multistep Thermal Annealing Process</i> , Thin Solid Films, Vol. 167, Pages 101-106, January 1, 1998	

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